

P27139.A03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kangguo CHENG

Group Art Unit: 2812

Serial No:10/710,608

Examiner: Bradley SMITH

Filed: July 23, 2004

For: **PATTERNED STRAINED SEMICONDUCTOR SUBSTRATE AND DEVICE**

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
U.S. Patent and Trademark Office
Customer Service Window, Mail Stop Amendment
Randolph Building
401 Dulany Street
Alexandria VA 22314

Sir :

In accordance with the duty of disclosure under 37 C.F.R. § 1.56 and supplemental to the Information Disclosure Statement filed on July 23, 2004 and August 23, 2005, applicant respectfully brings the following documents, listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application.

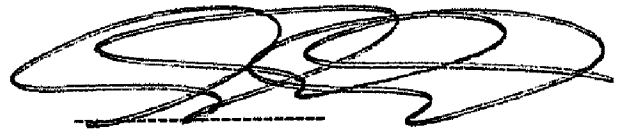
Further to the U.S. Patent and Trademark Office's decision to waive the requirement under 37 C.F.R. § 1.98 (a)(2)(i), copies of the U.S. patents and U.S. published patent applications are not enclosed herewith. However, if any copies are needed, the Examiner is respectfully requested to contact the undersigned.

Applicant respectfully requests that the Examiner consider the materials cited and indicate such consideration by appropriately initialing the enclosed PTO-1449 Form and including a copy of the initialed form in the next official communication.

P27139.A03

Should there be any questions concerning this application, the Examiner is invited to contact the undersigned at the below listed telephone number.

Respectfully submitted,
Kangguo CHENG

A handwritten signature in black ink, appearing to read 'Andrew M. Calderon', written over a horizontal dashed line.

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FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No.		Application No. 10/710,608	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Kangguo CHENG et al.			
				Filing Date 07/23/2004		Group 2812	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2002/0063292 A1	5-30-2002	Armstrong et al.			
		US 2003/0032261 A1	2-13-2003	Yeh et al.			
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
		JP 64-76755	3-22-1989	Japan		-	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office			Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)					Applicant			
					Filing Date		Group	
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.						
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EXAMINER					DATE CONSIDERED			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								